



SOT-23 Plastic-Encapsulated Diodes

1SS187 SWITCHING DIODE

FEATURES

Power dissipation

$$P_D : 150 \text{ mW} (T_{amb}=25^\circ\text{C})$$

Forward Current

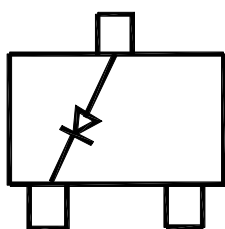
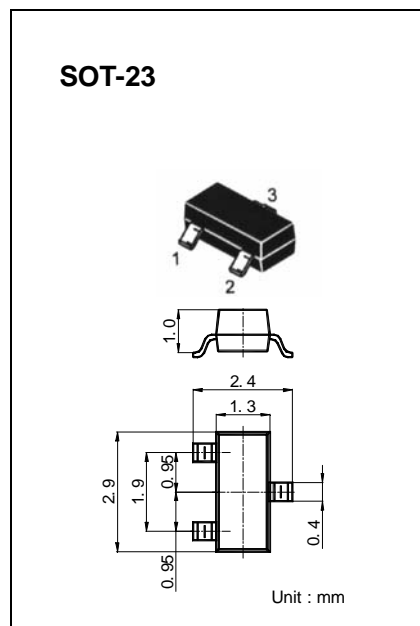
$$I_F : 100 \text{ mA}$$

Reverse Voltage

$$V_R : 80 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$



Marking DB

ELECTRICAL CHARACTERISTICS($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|---------------------------------|------------|-------------------------------------|-----|-----|---------------|
| Reverse breakdown voltage | $V_{(BR)}$ | $I_R = 100\mu\text{A}$ | 80 | | V |
| Reverse voltage leakage current | I_R | $V_R = 80\text{V}$ | | 0.5 | μA |
| Forward voltage | V_F | $I_F = 100\text{mA}$ | | 1.2 | V |
| Diode capacitance | C_D | $V_R = 0\text{V}$ $f = 1\text{MHz}$ | | 4 | pF |
| Reverse recovery time | t_{rr} | | | 4 | nS |